

Triac

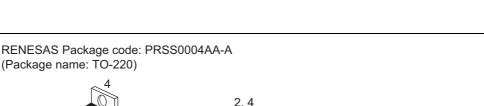
Medium Power Use

REJ03G0299-0300 Rev.3.00 Nov 30, 2007

Features

- I_{T (RMS)} : 20 A
- V_{DRM}: 600 V
- I_{FGTI} , I_{RGTI} , $I_{RGT III}$: 30 mA (20 mA)^{Note6}

Outline

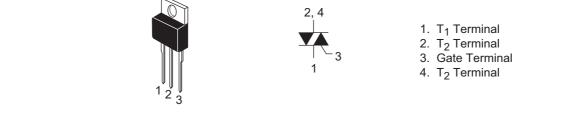


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Non-Insulated Type

Planar Passivation Type



Applications

Vacuum cleaner, electric heater, light dimmer, copying machine, and controller for other motor and heater

Maximum Ratings

Parameter	Symbol	Voltage class	Unit	
Falanielei	Symbol	12		
Repetitive peak off-state voltage ^{Note1}	V _{DRM}	600	V	
Non-repetitive peak off-state voltage ^{Note1}	V _{DSM}	720	V	

BCR20AM-12LA

Parameter	Symbo I	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	20	A	Commercial frequency, sine full wave 360° conduction, Tc = $109^{\circ}C^{Note3}$
Surge on-state current	I _{TSM}	200	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	167	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P _{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I _{GM}	2	А	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	– 40 to +125	°C	
Mass		2.0	g	Typical value

Notes: 1. Gate open.

Electrical Characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state cu	rrent	I _{DRM}	_	—	2.0	mA	Tj = 125°C, V _{DRM} applied
On-state voltage		V _{TM}	_	_	1.5	V	Tc = 25° C, I _{TM} = 30 A, Instantaneous measurement
Gate trigger voltage ^{Note2}	Ι	V_{FGTI}		_	1.5	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	V _{RGTI}	_	—	1.5	V	R _G = 330 Ω
	III	V _{RGTIII}	—	—	1.5	V	
Gate trigger current ^{Note2}	Ι	I _{FGTI}	_	—	30 ^{Note6}	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	I _{RGTI}	_	—	30 ^{Note6}	mA	R _G = 330 Ω
	III	I _{RGTIII}	_	_	30 ^{Note6}	mA	
Gate non-trigger voltage		V_{GD}	0.2	—	—	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	_	—	0.8	°C/W	Junction to case ^{Note3 Note4}
Critical-rate of rise of off-sta commutating voltage ^{Note5}	te	(dv/dt)c	10	—	—	V/µs	Tj = 125°C

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. Case temperature is measured at the T_2 tab 1.5 mm away from the molded case.

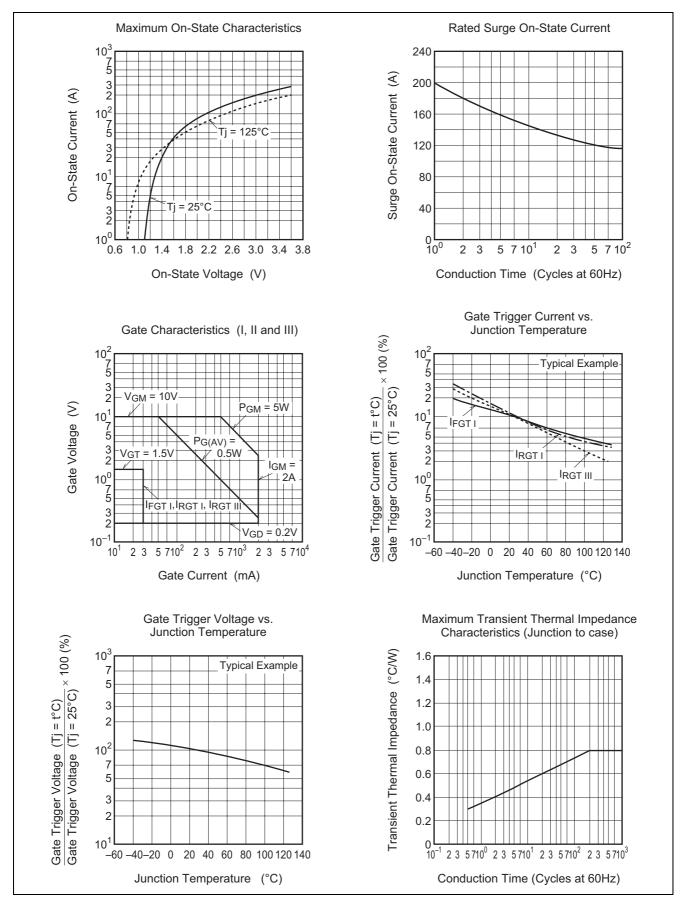
4. The contact thermal resistance $R_{th\,(c\text{-}f)}$ in case of greasing is 1.0°C/W.

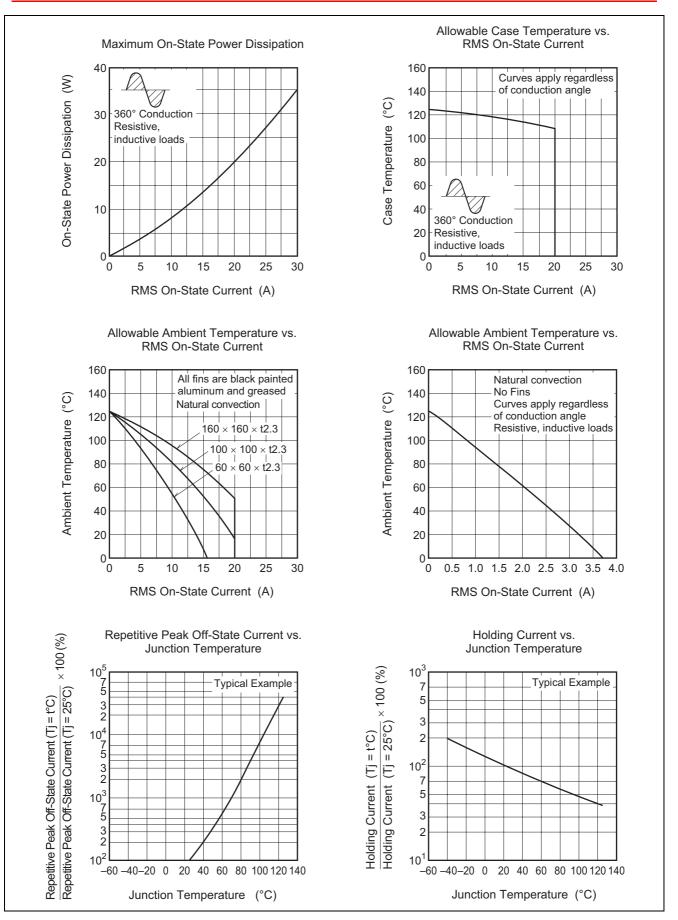
5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

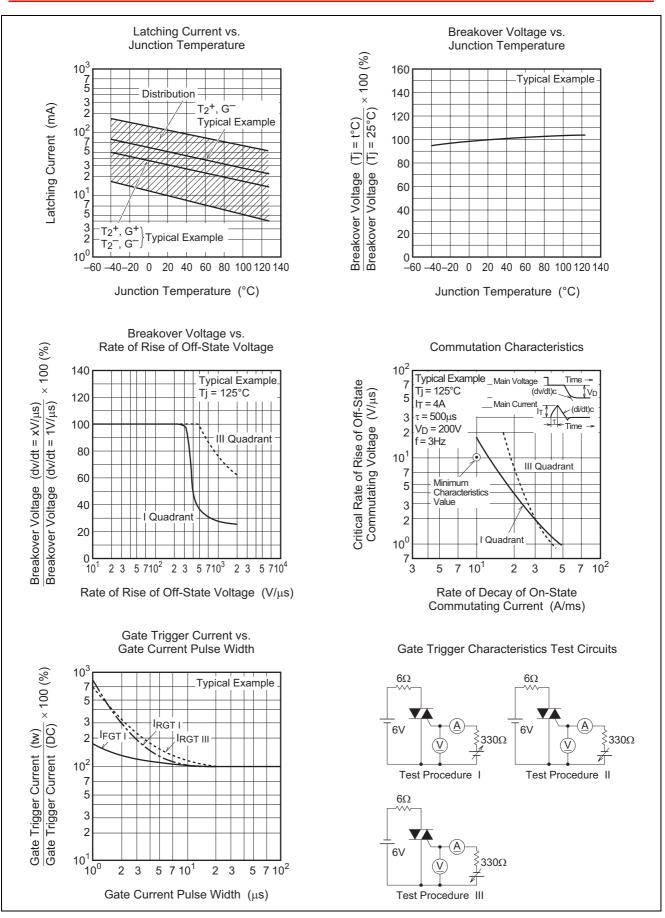
6. High sensitivity ($I_{GT} \le 20$ mA) is also available. (I_{GT} item: 1)

Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C	Supply Voltage		
2. Rate of decay of on-state commutating current (di/dt)c = -10 A/ms	Main Current → Time		
3. Peak off-state voltage V _D = 400 V	Main Voltage Time (dv/dt)c V _D		

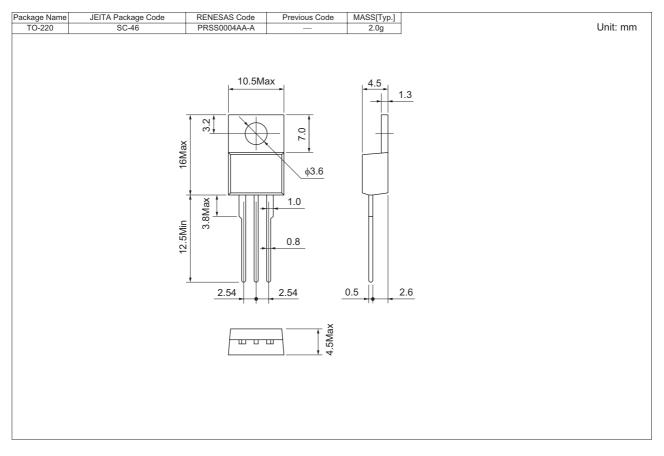
Performance Curves







Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR20AM-12LA
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR20AM-12LA-A8

Note : Please confirm the specification about the shipping in detail.

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